

The following configurations are available:



DESCRIPTION:

The Central Semiconductor CMPD5001 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for switching applications requiring extremely high current capability.

CMPD500 ²	1 SINGLE	MARKING CO	DE: DA2		
CMPD500	1S DUAL, IN S	ERIES MARKING CO	DE: D49		
MAXIMUM	RATINGS: (T _A =25°C)				
		SYMBOL			UNITS
Continuous Reverse Voltage		V _R	120		V
Continuous Forward Current		١F	400		mA
Peak Repetitive Forward Current		IFRM	800		mA
Peak Repetitive Reverse Current		IRRM	600		mA
Forward Su	rge Current, tp=1.0 μs	IFSM	6.0		A
Forward Su	rge Current, tp=1.0 s	IFSM	1.5		A
Power Dissipation		PD	350		mW
Operating a	nd Storage				
Junction Temperature		T _J , T _{stg}	-65 to +	150	°C
Thermal Resistance		Θ_{JA}	357		°C/W
ELECTRICA	AL CHARACTERISTICS	PER DIODE: (T _A =25°C unles	s otherwise note	ed)	
SYMBOL	TEST CONDITIONS		MIN	MAX	UNITS
BVR	I _R =1.0mA		120	175	V
I _R	V _R =90V			100	nA
IR	V _R =90V, T _A =150°C			100	μA
V _F	I _F =10mA			0.75	V
VF	I _F =50mA			0.84	V
VF	I _F =100mA			0.90	V
VF	I _F =200mA			1.00	V
VF	I _F =400mA			1.25	V
CT	V _R =0V, f=1.0 MHz			35	pF
t _{rr}	I _R =I _F =30mA, Rec. to 3	3.0mA, R _L =100Ω		60	ns
t _{rr}	$I_R=I_F=10$ mA, Rec. to 3.0mA, $R_L=100\Omega$			50	ns

R1 (26-September 2002)



CMPD5001 CMPD5001S

HIGH CURRENT INDUCTIVE LOAD SWITCHING DIODE

SOT-23 CASE - MECHANICAL OUTLINE





DIMENSIONS								
	INC	HES	MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
А	0.003	0.007	0.08	0.18				
В	0.006	-	0.15	-				
С	-	0.005	-	0.13				
D	0.035	0.043	0.89	1.09				
Е	0.110	0.120	2.80	3.05				
F	0.075		1.90					
G	0.037		0.95					
Н	0.047	0.055	1.19	1.40				
	0.083	0.098	2.10	2.49				
J	0.014	0.020	0.35	0.50				

SOT-23 (REV: R3)

R1 (26-September 2002)